

# ControlNet™ TRANSCEIVER

Check for Samples: SN65HVD61

### **FEATURES**

- Compatible With the ControlNet Standard
- I/O Operates From 2.5-V to 5-V Supply
- Receiver thresholds within -120mV to 120mV
- Receiver hysteresis >50mV
- Low Power Standby Mode
- **Thermal Shutdown Protection**
- Power-Up/Down Glitch-free Bus Inputs and **Outputs**
- **Short-Circuit Protection on Outputs**
- **RoHS Compliant**
- **ControlNet Vendor ID 806**

## DESCRIPTION

SN65HVD61 is designed to meet the requirements for the driver and receiver circuitry of the ControlNet coaxial-based physical layer.

These devices are single-channel circuits with one transceiver for single node operation or distributed stand-alone applications.

The pull-or-pull transmitter circuit is designed to sink current from a center-tapped transformer, providing galvanic isolation from the shared bus.

These devices incorporate a differential receiver (RX) with the 120 mV sensitivity needed by ControlNet industrial applications.

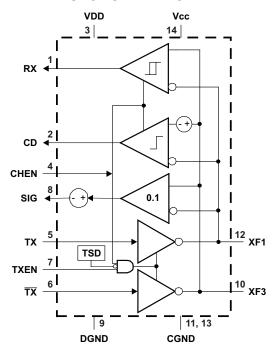
A secondary receiver (CD) detects the presence of a valid positive differential signal.

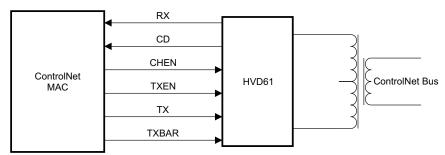
The third signal receiver function (SIG) provides a scaled analog output which is proportional to the differential voltage between XF1 and XF3. This output can be used for diagnostic purposes.

#### APPLICATIONS

- **Industrial Networks**
- **Programmable Controllers**
- **Industrial Drives**

#### **FUNCTIONAL DIAGRAM**





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet. ControlNet is a trademark of ODVA.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### ORDERING INFORMATION

PART NUMBER	PACKAGE <sup>(1)</sup>	MARKED AS
CNICELIVIDO4	D	CELIV/DC4
SN65HVD61	DR <sup>(2)</sup>	65HVD61

- For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.
- R suffix indicates tape and reel

## ABSOLUTE MAXIMUM RATINGS(1)

				VALUE	UNIT
V <sub>CC</sub>	Supply voltage (2) (3)			-0.3 to 6	V
$V_{DD}$	Supply voltage <sup>(4)</sup>			-0.3 to 6	V
	Logic input voltage range (TX, TXBAR , TXEN, CHEN)				V
	Bus terminal voltage range (XF1, XF3)				V
	Logic input current, (TX, TXBAR , TXEN, CHEN)				mA
	Bus terminal current (XF1, XF3)				
	Receiver output current (RX, C	CD)		±15	mA
		11	Bus pins (XF1, XF3)	16	kV
		Human Body Model (4)	All other pins	4	kV
	Electrostatic discharge	Charged Device Model (5)	All mins	1500	V
		Machine Model <sup>(6)</sup>		200	V
TJ	Junction temperature (see <sup>(7)</sup> below regarding thermal shutdown)				°C

- (1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- DGND and CGND should be connected to a common ground plane external to the device. All voltage values, except differential I/O bus voltages, are with respect to the ground plane
- V<sub>CC</sub> and V<sub>DD</sub> lower limits are DC conditions, see application information regarding start-up transients.
- Tested in accordance JEDEC Standard 22, Test Method A114-A.
- Tested in accordance JEDEC Standard 22, Test Method C101. Tested in accordance JEDEC Standard 22, Test Method A115-A.
- If the internal junction temperature exceeds 170°C, a thermal shutdown function will disable the transmitter.

#### DISSIPATION RATINGS

CIRCUIT BOARD MODEL <sup>(1)</sup>	T <sub>A</sub> ≤ 25°C	DERATING FACTOR (2) ABOVE T <sub>A</sub> = 25°C	T <sub>A</sub> = 65°C	T <sub>A</sub> = 100°C
Low-K	625 mW	5 mW/°C	425 mW	250 mW
High-K	1180 mW	9.5 mW/°C	800 mW	475 mW

- Tested in accordance with the Low-K or High-K thermal metric definitions of EIA/JESD51-3 for leaded surface mount packages. For additional information about JEDEC thermal models, see Texas Instruments Application Note Thermal Characteristics of Logic and Linear Packages using JEDEC PCB Designs (SZZA017).
- This is the inverse of the junction-to-ambient thermal resistance when board-mounted and with no air flow.



# **RECOMMENDED OPERATING CONDITIONS**

			MIN	NOM	MAX	UNIT
$V_{CC}$	Analog supply voltage (1)		4.5	5	5.5	V
$V_{DD}$	Input/Output supply voltage (2)		2.375		5.5	V
V <sub>IH</sub>	High-level logic input voltage	TV TVDAD TVEN CHEN	0.7×VDD		VDD	\/
$V_{IL}$	Low-level logic input voltage	TX, TXBAR, TXEN, CHEN	0	C	0.3×VDD	V
	Bus pin common-mode voltage	(VXF1 + VXF3 ) / 2	4.5		5.5	V
	Voltage at any bus terminal (XF1, XF3)		-10		15	V
	Transmitter peak output current (XF1, XF3)			130	150	mA
I <sub>OH</sub>	High-level logic output current	DV 0D	-8			Λ
I <sub>OL</sub>	Low-level logic output current	RX, CD			8	mA
	Output current	SIG	-1		1	mA
T <sub>A</sub>		4.75 V ≤ V <sub>CC</sub> ≤ 5.25 V	-40		100	
	Operating free-air temperature	4.5 V ≤ V <sub>CC</sub> ≤ 5.5 V	-30		100	°C
TJ	Junction temperature				150	
	Signaling rate			10		Mbps
	Relative humidity (non-condensing	1)			95%	

 <sup>(1)</sup> A power-shutdown feature keeps the device disabled when the voltage at V<sub>CC</sub> is below 2.1 V.
 (2) The I/O ring voltage for this device (V<sub>DD</sub>) should be the same as the power supply voltage for the controller with which it interfaces. In the case where the voltages are different, designers must consider the logic threshold compatibility between devices.



## **ELECTRICAL CHARACTERISTICS**

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDI	TIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT
BUS PINS	S (XF1, XF3)						
V <sub>OL(TX)</sub>	Transmitter output low voltage	Connect to V <sub>CC</sub> through			0.9	1.2	V
V <sub>OH(TX)</sub>	Transmitter output high voltage	37.5 Ω, ±1% resistor		V <sub>CC</sub> -0.05	$V_{CC}$		V
V <sub>O(OFF)</sub>	Transmitter off noise level,  XF3-XF1		$R_L = 37.5~\Omega,~0$ to 20 MHz BW, TX and TXBAR inputs idle, CHEN and TXEN inputs LO			5	mV
V <sub>SW(PP)</sub>	Receiver-to-bus reflection, peak-to-peak	R1=R2=50 Ω, C1=C2=15pF, S	See Figure 3			200	mV
V <sub>TH+</sub>	Positive-going differential input threshold voltage	4.5V < Vcm < 5.5V			35	120	mV
V <sub>TH-</sub>	Negative-going differential input threshold voltage	4.5V < Vcm < 5.5V		-120	-35		mV
V <sub>hys</sub>	Hysteresis voltage (V <sub>TH+</sub> – V <sub>TH-</sub> )	4.5V < Vcm < 5.5V, RX outpu	t	50	70		mV
V <sub>CD</sub>	Carrier detect threshold voltage, (XF3–XF1)	4.5V < Vcm < 5.5V		23	175	255	mV
I <sub>I</sub>	Bus terminal input leakage current	V <sub>I</sub> = 10V, TXEN at 0V, Other input at –10V to 10V				1.2	mA
"	Duo tommai mpat isanago sanoni	$V_1 = -10V$ , TXEN at 0V Other input at -10V to 10V		-1.7			
I <sub>I(off)</sub>	Bus terminal input leakage current	$V_{CC}$ < 2V, $V_I$ = -10V to 10V Other input at -10 V to 10 V		-1.7		1.2	mA
Ios	Short-circuit output current	0 < V <sub>O</sub> < V <sub>CC</sub>		-400		400	mA
R <sub>IN</sub>	Bus terminal input resistance	$V_I = -10V$ to 10V, Other input	at CGND, DC	12			kΩ
C <sub>IN</sub>	Differential input capacitance (XF1-to-XF3)	10 MHz AC test frequency, 1V <sub>PP</sub> amplitude using HP4194A or equivalent impedance analyzer, V <sub>CC</sub> = 0V			7	11	pF
LOGIC IN	IPUTS (TX, TXBAR, TXEN,CHEN)						
l <sub>l</sub>	Logic input current	TX, TXBAR, TXEN, CHEN		-100		100	μΑ
I <sub>I(off)</sub>	Logic input power-off current	V <sub>DD</sub> at 0 V, TX,TXBAR, TXEN	, CHEN		-100	100	μΑ
	UTPUTS (RX, CD)						
	Lania autoritualtana hink laval	C <sub>L</sub> = 15 pF		0.8×V <sub>DD</sub>			
V <sub>OH</sub>	Logic output voltage, high level	$I_{O} = -4 \text{ mA}, V_{DD} > 3V$		2.4			V
	Landa autorituralta da Januara	C <sub>L</sub> = 15 pF				$0.2 \times V_{DD}$	V
V <sub>OL</sub>	Logic output voltage, low level	I <sub>O</sub> = 4 mA				0.4	V
l <sub>oz</sub>	Logic output high-impedance-state current	RX, CD, 0 < V <sub>O</sub> < V <sub>DD</sub>		-20		20	μΑ
I <sub>O(off)</sub>	Logic output power-off current	V <sub>DD</sub> at 0 V, 0 < V <sub>O</sub> < 5.5V		-1		1	mA
	STRENGTH PIN (SIG)		-			*	
V <sub>SIG(0)</sub>	SIG output voltage with zero differential input voltage	$R_L = 5 \text{ k}\Omega$		1.125	1.25	1.375	V
		V <sub>ID</sub> switching at 10 Mbps,	4.75V ≤ V <sub>CC</sub> ≤ 5.25V			120	
GAIN	SIG gain ΔV <sub>O</sub> /ΔV <sub>ID</sub>	V <sub>O</sub> measured with 20 MHz bandwidth, See Figure 10	4.5V ≤ V <sub>CC</sub> ≤ 5.5V			140	mV/V
POWER S	SUPPLY PINS (V <sub>CC</sub> , CGND, VDD, DGND)		· · · · · · · · · · · · · · · · · · ·			'	
	Analog supply current (dynamic)	CHEN and TXEN at logic high, No load			36	65	
laa	Analog supply current, chip disabled	CHEN at logic low  CHEN at DGND, TX and TXBAR at V <sub>DD</sub>			1.8	3	m۸
Icc	Analog supply current, Lowest power conditions				0.8	2	mA
	I/O supply current, I/O, dynamic	CHEN at logic high, no load				5	mA
$I_{DD}$	I/O supply current, I/O, chip disabled	CHEN at logic low				105	μA

<sup>(1)</sup> All typical values are at 25°C and with a 5 V supply. For typical values with a 3.3V supply, refer to the TYPICAL CHARACTERISTICS curves.



# **SWITCHING CHARACTERISTICS**

over operating recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CO	ONDITIONS	MIN	TYP	MAX	UNIT
TRANSI	MITTER						
t <sub>r</sub>	Output rise time (10%-to-90%) differential				20	30	
t <sub>f</sub>	Output fall time (90%-to-10%) differential			20	30		
t <sub>PLH</sub>	Propagation delay time, low-to-high-level differential output	$R_L = 37.5 \Omega, C_L = 1$			22	50	ns
t <sub>PHL</sub>	Propagation delay time, high-to-low-level differential output	TXEN at logic high,	See Figure 1 (1)		24	50	110
t <sub>sk(p)</sub>	Pulse skew, differential (XF3-XF1)   t <sub>PLH</sub> - t <sub>PHL</sub>				2	5	
t <sub>OUT</sub> SKEW	Output delay skew, $t_{\text{pON}} - t_{\text{pOFF}}$ , single-ended outputs	$R_L = 37.5 \Omega, C_L = 1$	5 pF, CHEN and	0	7	12	no
t <sub>ON</sub> -t <sub>OFF</sub>	Symmetry, turn-on-time-to-turn-off-time, 10%/90%, each single-ended output	TXEN at logic high, See Figure 2		0	9	12	ns
t <sub>PZL</sub>	Propagation delay time, disabled-to-low-level output		TXEN changing,			250	
$t_{PLZ}$	Propagation delay time, low-level-to-disabled-output	$R_L = 37.5 \Omega,$ CHEN at VDD $C_L = 15 \text{ pF}$ , See Figure 4 CHEN changing,	CHEN at VDD			400	no
$t_{PZL}$	Propagation delay time, disabled-to-low-level output		CHEN changing,			400	ns
t <sub>PLZ</sub>	Propagation delay time, low-level-to-disabled-output		TXEN at VDD			400	
SR	Output differential slew rate	See Figure 1	0°C < T < 85°C			1	V/ns
	Transmit jitter, differential	10 Mbps Mancheste	er-code		2.5		ns
RECEIV	ERS (RX and CD)						
t <sub>r</sub>	Output rise time (10%-to-90%)				2	20	
t <sub>f</sub>	Output fall time (90%-to-10%)	$V_{ID} = \pm 2.5 V$ ,			2	20	
t <sub>PLH</sub>	Propagation delay time, low-to-high-level output	$V_{ID} = \pm 2.5 V$ , $R_L = 1 \text{ k}\Omega$ ,			25	40	ns
t <sub>PHL</sub>	Propagation delay time, high-to-low-level output	C <sub>L</sub> = 15 pF, See Figure 5			25	40	115
	Pulse skew  tpl.H - tpHL	See Figure 5	RX		0.2	4.5	
t <sub>sk(p)</sub>	ruise skew  tpLH - tpHL		CD			7	
t <sub>PZL</sub>	Propagation delay time,high-impedance-to-low-level output	$V_{ID} = -2.5V, R_L = 1$	kΩ, C <sub>L</sub> = 15 pF,			1000	ne
$t_{PLZ}$	Propagation delay time,low-level-to-high-impedance output	See Figure 6				55	ns
t <sub>PZH</sub>	Propagation delay time, high-impedance-to-high-level output	$V_{ID} = 2.5V, R_L = 1ks$	$\Omega$ , $C_L = 15 pF$ ,			1000	·
t <sub>PHZ</sub>	Propagation delay time, high-level-to-high- impedance output	See Figure 7				55	ns
	Receive jitter	10 Mbps Mancheste	er-code		0.5		

<sup>(1) 30</sup> ns maximum represents the worst-case allowable rise/fall time when connected to a transformer-coupler network.



## PARAMETER MEASUREMENT INFORMATION

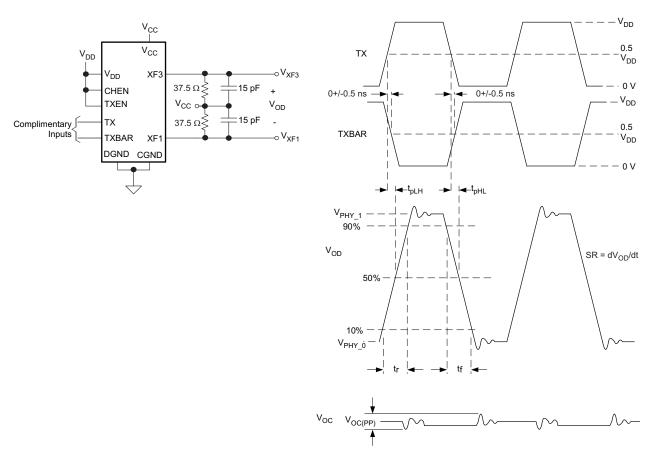


Figure 1. Transmitter Differential Switching Characteristics

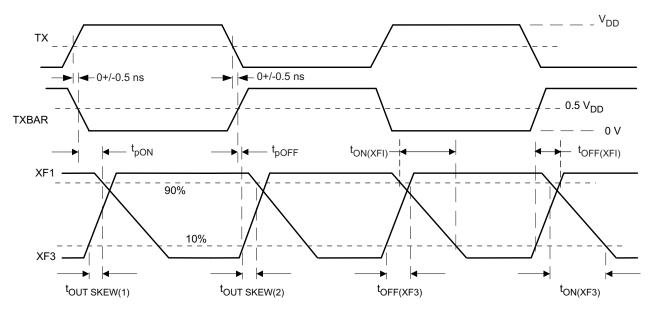


Figure 2. Transmitter Single-Ended Switching Characteristics



# PARAMETER MEASUREMENT INFORMATION (continued)

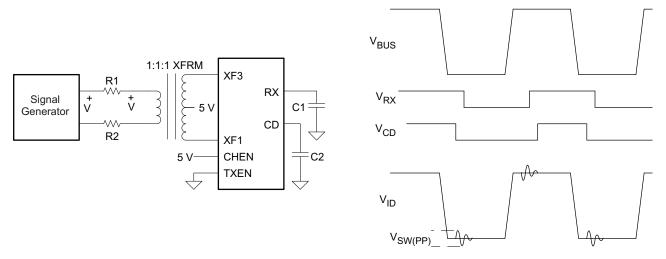


Figure 3. Receiver-to-Bus Reflection Measurement

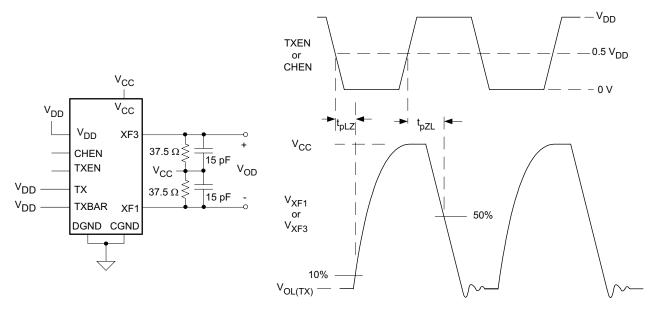


Figure 4. Transmitter Enable/Disable Test Circuits and Characteristics



# PARAMETER MEASUREMENT INFORMATION (continued)

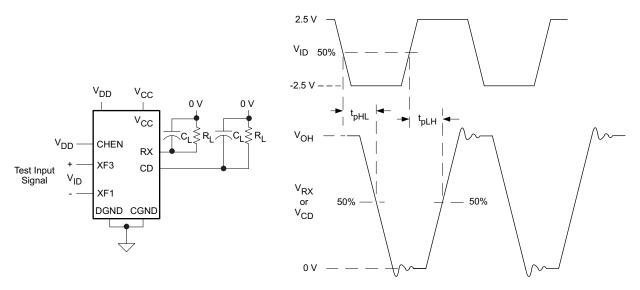


Figure 5. Test Circuit and Signal Waveforms, Receiver and Carrier Detect

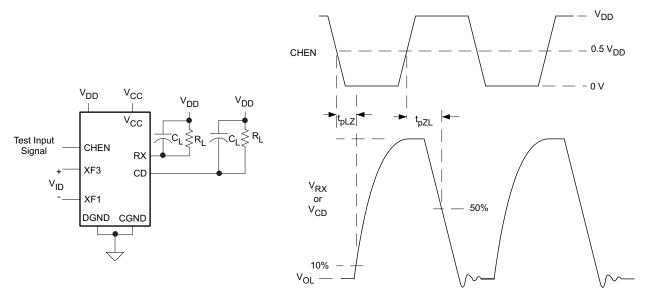


Figure 6. Test Circuit and Signal Waveforms, Receiver Enable and Disable With Low Bus Input



# **PARAMETER MEASUREMENT INFORMATION (continued)**

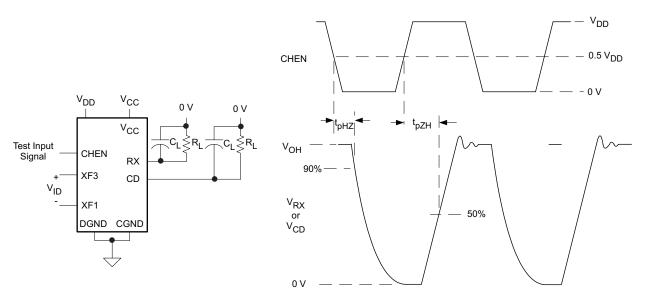


Figure 7. Test Circuit and Signal Waveforms, Receiver Enable and Disable With High Bus Input

**Table 1. FUNCTION TABLES** 

	TRANSMITTER					
	INPUTS				PUTS	
CHEN	TXEN	TX	TXBAR	XF1	XF3	
L or OPEN	X	Х	X	Z	Z	
	L or OPEN	Х	X	Z	Z	
		L or OPEN	L or OPEN	Z	Z	
Н	Н	L or OPEN	Н	Z	L	
		Н	L or OPEN	L	Z	
	H <sup>(1)</sup>	H <sup>(1)</sup>	H <sup>(1)</sup>	L <sup>(1)</sup>	L <sup>(1)</sup>	

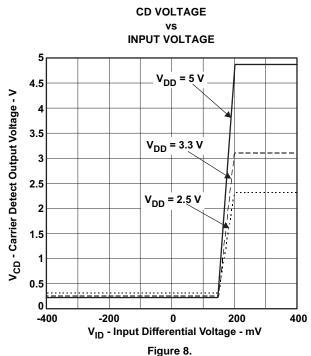
(1) This combination is not supported and should be avoided in ControlNet applications

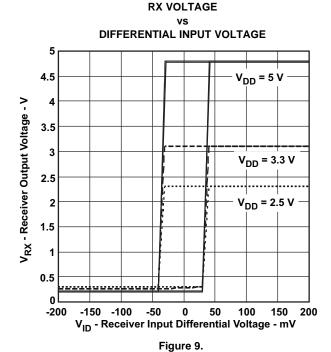
	RECEIVER					
	INPUTS					
CHEN	XF1, XF3	CONDITION	RX			
L or OPEN	X	Chip disabled	Z			
	$(V_{XF3} - V_{XF1}) < V_{TH-}$	Negative signal	L			
Н	$V_{TH-} < (V_{XF3} - V_{XF1}) < V_{TH+}$	No signal	?			
	$V_{TH+} < (V_{XF3} - V_{XF1})$	Positive signal	Н			

	CARRIER DETECT				
	INPUTS				
CHEN	XF1, XF3	CONDITION	CD		
L or OPEN	X	Chip disabled	Z		
	$(V_{XF3} - V_{XF1}) < V_{CD}$	Carrier not detected	L		
	$V_{CD} < (V_{XF3} - V_{XF1})$	Carrier detected	Н		



## **TYPICAL CHARACTERISTICS**





SIG VOLTAGE
VS
DIFFERENTIAL INPUT VOLTAGE

2.5

10 Mbps Signaling Rate

2

1.5

0.5

0.5

V<sub>ID</sub> - Differential Input Voltage - V

Figure 10.

10



#### APPLICATION INFORMATION

#### THERMAL SHUTDOWN

In most cases, the device's internal junction temperature will not reach the thermal shutdown temperature if operated within the recommended operating conditions. However, during fault conditions, such as driver short-circuit, the junction temperature may reach the thermal shutdown limit. This also depends on the thermal characteristics of the device mounting, the circuit board, and environmental factors. After the device reaches the thermal shutdown temperature, the driver outputs will be disabled, and the device will cool down. If the short-circuit is still present when the drivers are re-enabled, this *thermal shutdown cycle* will repeat until the short-circuit fault is removed.

For long-term reliability, the package power dissipation must not exceed the values in the data sheet POWER DISSIPATION RATINGS for extended periods.

# **POWER-UP TRANSIENTS**

The absolute maximum ratings for Vcc and Vdd specify the limits for these supplies. During initial power-on, these supply voltages may instantaneously drop below the given lower limit. Designers should consider that diodes in the circuitry will begin to turn on if the voltage becomes too negative, and that damage may occur if these diodes dissipate significant power internal to the device. The actual threshold for possible damage is a function of both undervoltage magnitude and undervoltage transient duration. Further, the allowable undervoltage transient conditions depend on factors such as device junction temperature and power supply source impedance.

#### THERMAL CHARACTERISTICS OF IC PACKAGES

Junction-to-Ambient Thermal Resistance ( $\theta_{JA}$ ) is defined as the difference in junction temperature to ambient temperature divided by the operating power.  $\theta_{JA}$  is NOT a constant and is a strong function of

- the PCB design (50% variation)
- altitude (20% variation)
- device power (5% variation)

 $\theta_{JA}$  can be used to compare the thermal performance of packages if the specific test conditions are defined and used. Standardized testing includes specification of PCB construction, test chamber volume, sensor locations, and the thermal characteristics of holding fixtures.  $\theta_{JA}$  is often misused when it is used to calculate junction temperatures for other installations.

TI uses two test PCBs as defined by JEDEC specifications. The low-k board gives average in-use condition thermal performance and consists of a single trace layer 25 mm long and 2-oz thick copper. The high-k board gives best case in-use condition and consists of 2 1-oz buried power planes with a single trace layer 25 mm long with 2-oz thick copper. A 4% to 50% difference in  $\theta_{JA}$  can be measured between these two test cards

Junction-to-case thermal resistance  $(\theta_{JC})$  is defined as difference in junction temperature to case divided by the operating power. It is measured by putting the mounted package up against a copper block cold plate to force heat to flow from die, through the mold compound into the copper block.

 $\theta_{JC}$  is a useful thermal characteristic when a heatsink is applied to package. It is NOT a useful characteristic to predict junction temperature as it provides pessimistic numbers if the case temperature is measured in a non-standard system and junction temperatures are backed out. It can be used with  $\theta_{JB}$  in 1-dimensional thermal simulation of a package system.

Junction-to-board thermal resistance ( $\theta_{JB}$ ) is defined to be the difference in the junction temperature and the PCB temperature at the center of the package (closest to the die) when the PCB is clamped in a cold-plate structure.  $\theta_{JB}$  is only defined for the high-k test card.



 $\theta_{JB}$  provides an overall thermal resistance between the die and the PCB. It includes a bit of the PCB thermal resistance (especially for BGA's with thermal balls) and can be used for simple 1-dimensional network analysis of package system.

	JEDEC High-K Model	JEDEC Low-K Model
$\theta_{JA}$	105.7°C/W	199.5°C/W
$\theta_{JB}$	52.3	52.3
$\theta_{ m JC}$	56.32°C/W	56.32°C/W

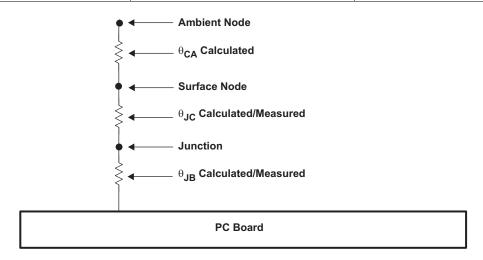


Figure 11. Thermal Resistance

Additional information about thermal metrics for integrated circuits is available in the Texas Instruments Application Note *IC Package Thermal Metrics* (SPRA953).

## **ControlNet APPLICATION**

In a typical ControlNet application, several nodes will be connected to a common bus, as shown in Figure 12. At any time, only one node should actively drive the bus; all active nodes continually receive the bus state. The node which is actively driving the bus will sink current through either the XF1 or XF3 terminal, causing the voltage on the bus to be either differential high or differential low.

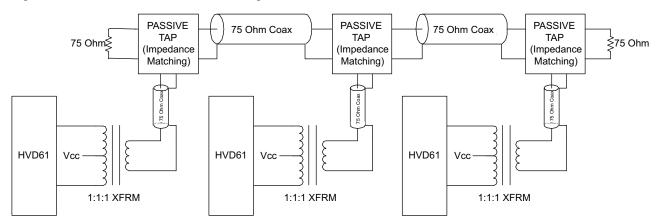


Figure 12. Typical ControlNet Application



#### SYSTEM-LEVEL EMC PROTECTION

The ControlNet network is intended to operate reliably in harsh industrial environments. At a system level, the network is tested according to several international electromagnetic compatibility (EMC) standards. The requirements are summarized in the Table 2 and Figure 13.

Table 2.	<b>EMC</b>	<b>Standard</b>	Requirements
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EMC STANDARD	DESCRIPTION OF TEST METHOD	LEVEL
IEC 61000-4-2	Electro Static Discharge (ESD) Immunity	6 kV Contact 8 kV Air-Gap
IEC 61000-4-3	Radiated Radio Frequency (RF) Immunity	10V/m at 80 MHz to 2.7GHz
IEC 61000-4-4	Fast Transients / Burst Immunity	1 kV
IEC 61000-4-5	Surge Immunity	1 kV
IEC 61000-4-6	Conducted Radio Frequency (RF) Immunity	10V at 150 kHz to 80 MHz 1kHz AM 80% modulation

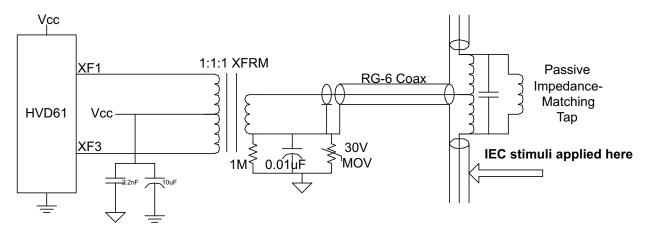


Figure 13. Simplified Test Set-Up for EMC Standards

# **DRIVER FUNCTIONS**

The ControlNet standard requires the transmitter to generate a signal with nominal amplitude of 8.2Vpp into a 37.5  $\Omega$  load. This applies to the double-terminated coax bus as shown in Figure 12. Rise and fall times should not exceed 30 nsec, and the signal slew rate should not exceed 1 V/nsec. Transmit signal distortion (ringing, droop, overshoot) should not exceed 10% of the peak-to-peak amplitude.

#### **RECEIVER FUNCTIONS**

The function of the primary receiver (RX) and the carrier detect (CD) depends on the signals XF1 and XF3. The purpose of RX is to indicate the status of the two ControlNet bus lines, based on the signals XF1 and XF3. If the voltage at XF3 is greater than the voltage at XF1, then the bus state is positive, and RX should output a HIGH voltage. This corresponds to a Phy\_1 symbol. If the voltage at XF3 is less than the voltage at XF1, then the bus state is negative, and RX should output a LOW voltage. This corresponds to a Phy\_0 symbol. See Figure 14. Note that the allowable variation in  $V_{TH-}$ ,  $V_{TH+}$ , and  $V_{CD}$  is specified in the ELECTRICAL CHARACTERISTICS table.



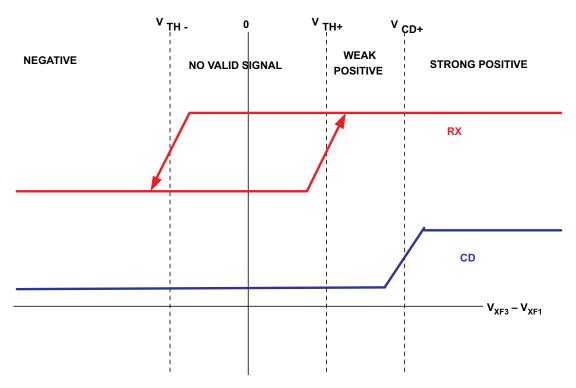


Figure 14. RX and CD Functions

# SIGNAL STRENGTH OUTPUT

Vsig should be sampled at the beginning of a transmission in the preamble portion of the ControlNet Frame. This portion is the same for all nodes with the exception of the amplitude. Sampling Vsig in the preamble will provide the most consistent measurement. Further oversampling coupled with multiple frame sampling may provide further cable diagnostics such as identifying reflections due to cable breaks. By sampling multiple times in the preamble of a packet the distance to the break or short may be calculated.



# **REVISION HISTORY**

NOTE: Page numbers of current version may differ from previous versions.

Ci	nanges from Revision C (May 2007) to Revision D	Page
•	Changed ControlNet is a trademark of ControlNet International, Ltd to ControlNet is a trademark of ODVA	1
•	Changed Vcc MIN from "4.75V" to "4.5V" and changed Vcc MAX from "5.25V" to "5.5V" in the ROC table	3
•	Changed V <sub>DD</sub> spec. MAX voltage from "5.25V" to "5.5V" in the ROC table	3
•	Changed Bus pin common-mode voltage MIN spec. from "4.75V to "4.5V" and MAX spec. from "5.25V to "5.5V" in the ROC table	3
•	Added second T <sub>A</sub> spec and condiitions in the ROC table	3
•	Changed V <sub>TH+</sub> spec. Test Conditions from "4.75V < Vcm < 5.25V" to "4.5V < Vcm < 5.5V"	4
•	Changed V <sub>TH</sub> . spec. Test Conditions from "4.75V < Vcm < 5.25V" to "4.5V < Vcm < 5.5V"	4
•	Changed V <sub>hys</sub> spec. Test Conditions from "4.75V < Vcm < 5.25V" to "4.5V < Vcm < 5.5V"	4
•	Changed V <sub>CD</sub> spec. Test Conditions from "4.75V < Vcm < 5.25V" to "4.5V < Vcm < 5.5V"	4
•	Changed I <sub>O(off)</sub> spec. Test Conditions maximum voltage from "5.25V" to "5.5V"	4
•	Added second GAIN spec with conditions of $4.5\text{V} \le \text{V}_{\text{CC}} \le 5.5\text{V}$ in the ELEC CHARA TABLE, and added 140 mV/V to the MAX column	4
•	Changed I <sub>DD</sub> (chip disabled) spec MAX from "10" to "105" μA	4
•	Added "0°C < T < 85°C" to Test Conditions for SR spec.	5
•	Deleted minimum spec value (1 ns) for Receivers (RX and CD) "Output rise time, t <sub>r</sub> and Output fall time, t <sub>f</sub> "	5
•	Changed RECEIVERS (RX and CD) t <sub>PLH</sub> spec and t <sub>PHL</sub> spec MAX value from "35" tp "40" ns	5
•	Changed t <sub>sk(p)</sub> spec MAX value from "3.5" to 4.5" for RX test condition	5
•	Changed RECEIVER t <sub>PLZ</sub> spec and t <sub>PHZ</sub> spec MAX value from "40" to "55" ns	5



# PACKAGE OPTION ADDENDUM

24-Apr-2015

#### **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	_	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
SN65HVD61D	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU   Call TI	Level-1-260C-UNLIM	-40 to 100	65HVD61	Samples
SN65HVD61DG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	-40 to 100	65HVD61	Samples
SN65HVD61DR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 100	65HVD61	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): Tl's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, Tl Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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# **PACKAGE OPTION ADDENDUM**

24-Apr-2015

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# D (R-PDSO-G14)

# PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.



# D (R-PDSO-G14)

# PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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